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PATENT

Attorney Docket No.: ASC-025DV2

Particulars of prior application:

Serial No.: 09/928,126

Filing Date: August 10, 2001

Examiner: C. Thompson of Art Unit 2813

Status: Allowed

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

APPLICANT: Cheng et al.

SERIAL NO.: Not yet assigned

GROUP NO.: Not yet assigned

FILING DATE: Herewith

EXAMINER: Not yet assigned

TITLE: PROCESS FOR PRODUCING SEMICONDUCTOR ARTICLE
USING GRADED EPITAXIAL GROWTH

BOX PATENT APPLICATION

Commissioner for Patents

Washington, D.C. 20231

PRELIMINARY AMENDMENT

Sir:

Please enter the following preliminary amendment before beginning examination of the above-identified divisional patent application.

AMENDMENTS

To the Title Page:

Please rewrite the title as --PROCESS FOR PRODUCING SEMICONDUCTOR ARTICLE USING GRADED EPITAXIAL GROWTH--.

To the Specification:

On page 2, please rewrite lines 1-2 as: --PROCESS FOR PRODUCING SEMICONDUCTOR ARTICLE USING GRADED EPITAXIAL GROWTH--.